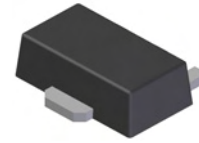


### Features

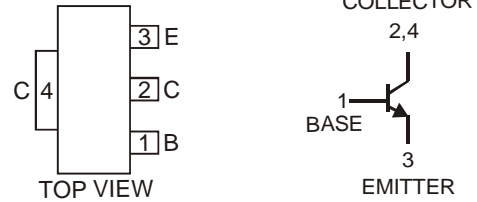
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

### Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



SOT89-3L



Schematic and Pin Configuration

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	2.0	A

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$	$P_D$	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
<b>OFF CHARACTERISTICS (Note 4)</b>						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25	—	—	V	$I_C = 1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	—	V	$I_C = 10\mu\text{A}, I_C = 0$
Collector-Base Cutoff Current	$I_{CBO}$	—	—	100	nA	$V_{CB} = 20\text{V}, I_E = 0$
Emitter-Base Cutoff Current	$I_{EBO}$	—	—	100	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
<b>ON CHARACTERISTICS (Note 4)</b>						
DC Current Gain	$h_{FE}$	200 65	— —	400 —	—	$V_{CE} = 2.0\text{V}, I_C = 0.1\text{A}$ $V_{CE} = 2.0\text{V}, I_C = 1.5\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.12	0.4	V	$I_C = 1.5\text{A}, I_B = 75\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	0.9	1.2	V	$I_C = 1.5\text{A}, I_B = 75\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current Gain-Bandwidth Product	$f_T$	—	300	—	MHz	$V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$
Output Capacitance	$C_{obo}$	—	16	—	pF	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$
<b>SWITCHING CHARACTERISTICS</b>						
Turn On Time	$t_{on}$	—	70	—	ns	$V_{CE} = 12\text{V}, V_{BE} = 5\text{V}, I_{B1} = I_{B2} = 25\text{mA}, I_C = 500\text{mA}$
Storage Time	$t_{stg}$	—	170	—	ns	
Fall Time	$t_f$	—	25	—	ns	

- Notes:
1. No purposefully added lead.
  2. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Measured under pulsed conditions. Pulse width = 300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

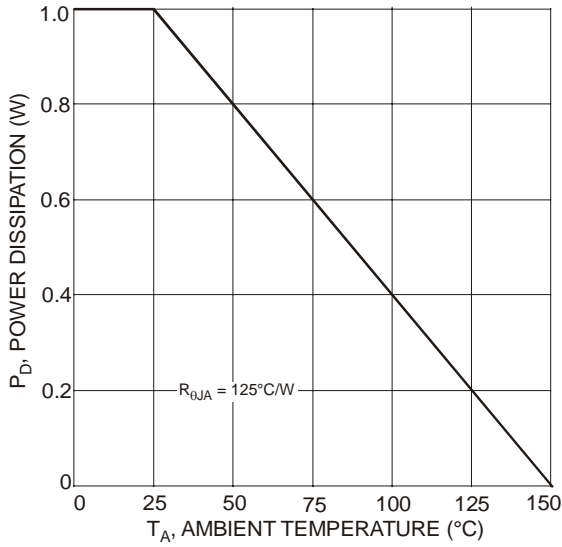


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

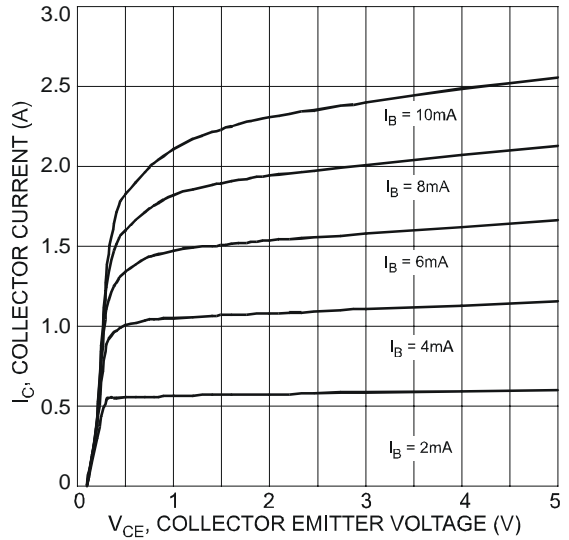


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

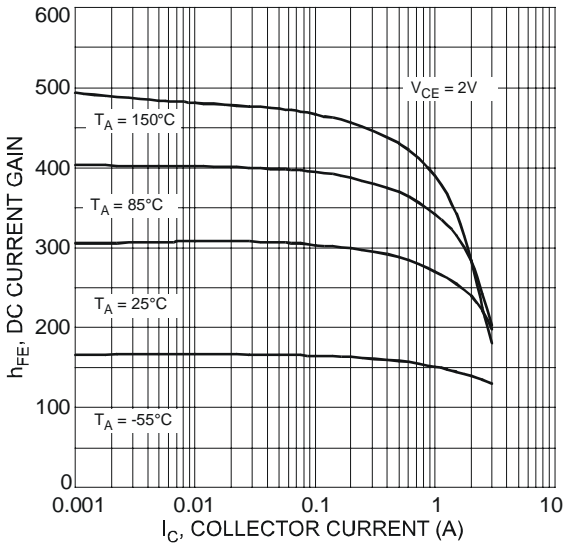


Fig. 3 Typical DC Current Gain vs. Collector Current

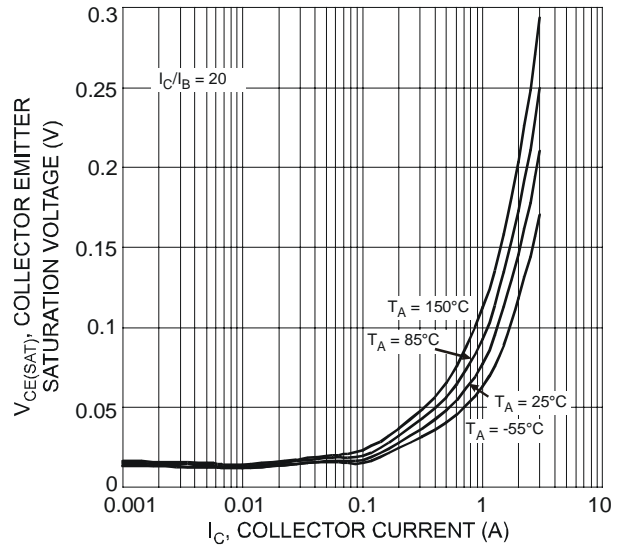


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

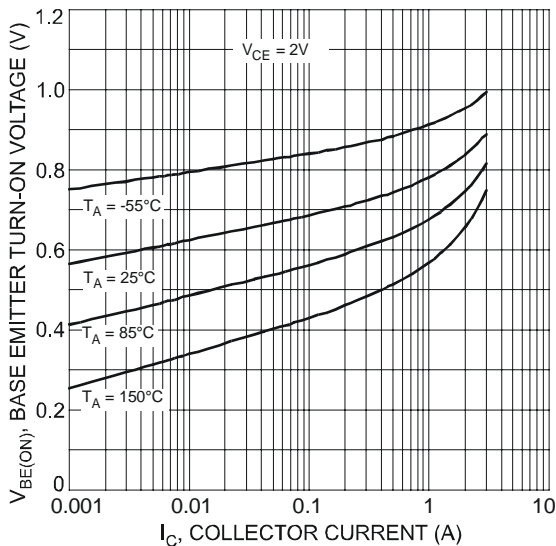


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

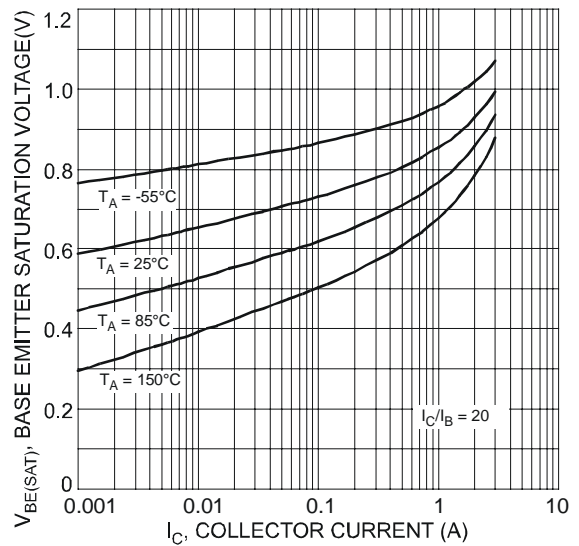
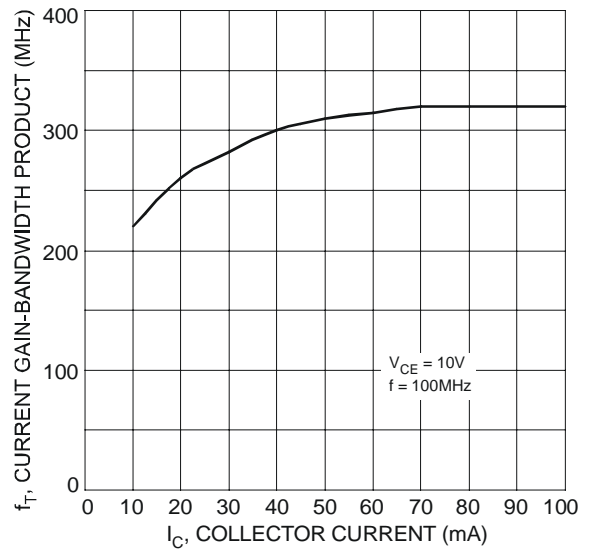
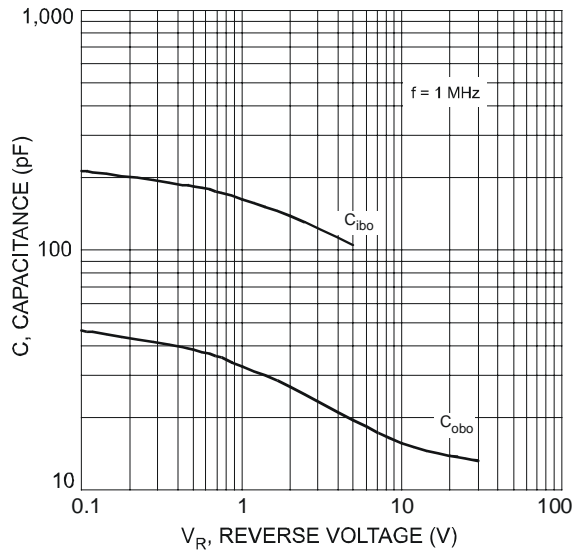


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

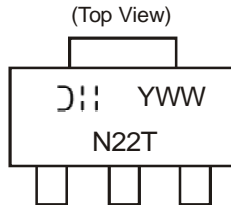


## Ordering Information (Note 5)

Device	Packaging	Shipping
2DD1621T-13	SOT89-3L	2500/Tape & Reel

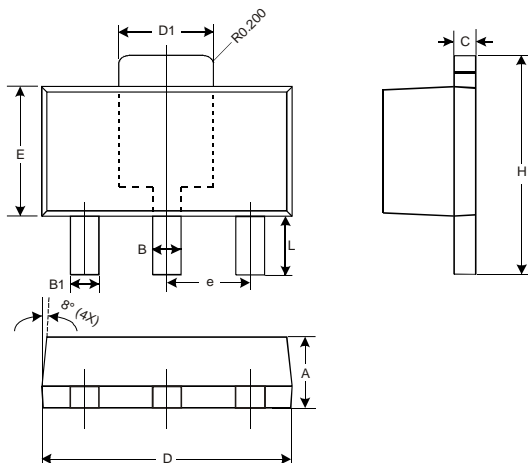
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap02007.pdf>.

## Marking Information



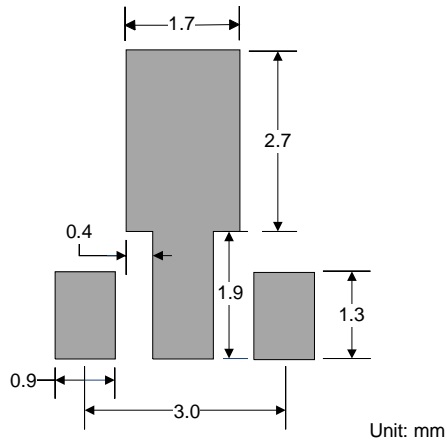
N22T = Product Type Marking Code  
 YWW = Date Code Marking  
 Y = Last digit of year ex: 7 = 2007  
 WW = Week code 01 - 52

## Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

## Suggested Pad Layout



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<http://moschip.ru/get-element>

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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